

WHAT IS CLAIMED IS:

1. A lithographic apparatus, comprising:
 - a radiation source configured to provide radiation to an illumination system, the radiation source configured to provide radiation in a first wavelength range and in a second wavelength range, the second wavelength range being different from the first wavelength range;
 - a support configured to support a patterning device, the patterning device configured to impart the radiation with a pattern in its cross-section;
 - a substrate table configured to hold a substrate;
 - a projection system configured to project the patterned radiation onto a target portion of the substrate.
2. A lithographic apparatus according to claim 1, wherein the radiation source further comprises a radiation source capable of providing radiation in both the first and second wavelength range, and a removable filter configured to provide the radiation in the first or second wavelength range.
3. A lithographic apparatus according to claim 1, wherein the radiation source further comprises a first radiation source element configured to provide radiation in the first wavelength range, and a second radiation source element configured to provide radiation in the second wavelength range, and a removable radiation director configured to direct radiation from the second radiation source element to the illumination system.
4. A lithographic apparatus according to claim 1, wherein the first wavelength range is a wavelength range used in a controlled environment, and the second wavelength range is a wavelength range used when the controlled environment is not established.
5. A lithographic apparatus according to claim 1, wherein the first wavelength range is in an EUV region.

6. A lithographic apparatus according to claim 5, wherein the first wavelength is about 13 nm.
7. A lithographic apparatus according to claim 1, wherein the first wavelength range is in a UV region.
8. A lithographic apparatus according to claim 7, wherein the first wavelength is in a region between about 157 nm to 193 nm.
9. A lithographic apparatus according to claim 1, wherein the second wavelength range is used for setup of the lithographic apparatus, the setup comprising one or more of calibration, qualification, performance test, and alignment.
10. A lithographic apparatus according to claim 1, wherein the substrate is exposed using the first wavelength range, and the second wavelength range is used for exposure of a further substrate.
11. A lithographic apparatus according to claim 1, wherein the second wavelength range is in a region between about 150 and 350 nm.
12. A device manufacturing method, comprising:
 - providing a substrate;
 - providing radiation at a first wavelength range and at a second wavelength range, the second wavelength range being different from the first wavelength range; and
 - patterning the radiation in its cross-section; and
 - projecting the patterned radiation onto a target portion of the substrate.
13. A method according to claim 12, further comprising filtering out radiation in the first or second wavelength range.
14. A method according to claim 12, further comprising directing radiation in the first or

second wavelength range to the illumination system.

15. A method according to claim 12, wherein the first wavelength range is a wavelength range in which radiation propagates in a controlled environment, and the second wavelength range is a wavelength range in which radiation propagates when the controlled environment is not established.

16. A method according to claim 12, wherein the first wavelength range is in an EUV region.

17. A method according to claim 16, wherein the first wavelength is about 13 nm.

18. A method according to claim 12, wherein the first wavelength range is in a UV region.

19. A method according to claim 18, wherein the first wavelength is in a region between about 157 nm to 193 nm.

20. A method according to claim 12, further comprising using the second wavelength range for setup of a lithographic apparatus, the setup comprising one or more of calibration, qualification, performance test, and alignment.

21. A method according to claim 12, further comprising using the first wavelength range for exposure of the substrate and using the second wavelength range for exposure of a further substrate.

22. A method according to claim 12, wherein the second wavelength range is in a region between about 150 and 350 nm.